

# 3DG8



## NPN Silicon High Frequency Low Power Transistor

### Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

### TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications				Test Condition
			A	B	C	D	
Total Dissipation	$P_{tot}$	mW	200				Ta=25°C
Max. Collector Current	$I_{CM}$	mA	30				
Junction Temperature	$T_{jm}$	°C	175				
Storage Temperature	$T_{stg}$	°C	-55~+175				
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	15	40	40	60	$I_C=0.1mA$
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	25	25	45	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4				$I_E=0.1mA$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5				$I_C=10mA$ $I_B=1mA$
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.0				
C-B Leakage Current	$I_{CBO}$	uA	0.1				$V_{CB}=10V$
C-E Leakage Current	$I_{CEO}$	uA	0.1				$V_{CE}=10V$
E-B Leakage Current	$I_{EBO}$	uA	0.1				$V_{EB}=1.5V$
DC Current Gain	$h_{FE}$		25~270				$V_{CE}=10V, I_C=3mA$
Transition frequency	$f_T$	MHz	150	150	300	300	$V_{CE}=10V, I_C=3mA$ $f=100MHz$

### hFE Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
$h_{FE}$	25~40	40~55	55~80	80~120	120~180	180~270

### Outline and Dimensions: